Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Package information	8
	3.1 H ² PAK-2 package information	ć
	3.2 H ² PAK-6 package information	2
4	Packing information	5
5	Revision history1	7



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	40	V
V _{GS}	Gate-source voltage	± 20	V
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25 °C	120	Α
I _D ⁽¹⁾	Drain current (continuous) at T _C = 100 °C	120	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	480	Α
P _{TOT}	Total dissipation at T _C = 25 °C	150	W
T _{stg}	Storage temperature	- 55 to 175	°C
Tj	Operating junction temperature	- 33 10 173	

^{1.} Current limited by package

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	1.0	°C/W
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max	35	°C/W

^{1.} When mounted on FR-4 board of 1 inch², 2 oz Cu.



2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$V_{GS} = 0$, $I_D = 250 \mu A$	40			V
	Zero gate voltage	$V_{GS} = 0, V_{DS} = 40 V$			1	μΑ
I _{DSS}	Drain current	$V_{GS} = 0$, $V_{DS} = 40$ V, $T_C = 125$ °C			100	μΑ
I _{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 20 \text{ V}$			± 100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3		4.5	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 60 A		1.9	2.4	mΩ

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance		-	7735	-	pF
C _{oss}	Output capacitance	$V_{GS} = 0, V_{DS} = 20 V,$	-	745	-	pF
C _{rss}	Reverse transfer capacitance	f = 1 MHz	-	560	-	pF
Qg	Total gate charge	V 00 V 1 400 A	-	130	-	nC
Q _{gs}	Gate-source charge	$V_{DD} = 20 \text{ V}, I_{D} = 120 \text{ A},$ $V_{GS} = 10 \text{ V}$	-	36	-	nC
Q_{gd}	Gate-drain charge	1.63	-	42	-	nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time		-	24	-	ns
t _r	Rise time	V _{DD} = 20 V, I _D = 60 A	-	150	-	ns
t _{d(off)}	Turn-off-delay time	$R_G = 4.7 \Omega V_{GS} = 10 V$	-	106	-	ns
t _f	Fall time		-	57	-	ns

4/18 DocID027534 Rev 1

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD} ⁽¹⁾	Source-drain current		-		120	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)		-		480	Α
V _{SD} (2)	Forward on voltage	V _{GS} = 0, I _{SD} = 120 A	-		1.3	٧
t _{rr}	Reverse recovery time	I _{SD} = 120 A, V _{DD} = 32 V	-	36		ns
Q _{rr}	Reverse recovery charge	di/dt = 100 A/µs,	-	40		nC
I _{RRM}	Reverse recovery current	T _j = 25 °C	-	2.3		Α

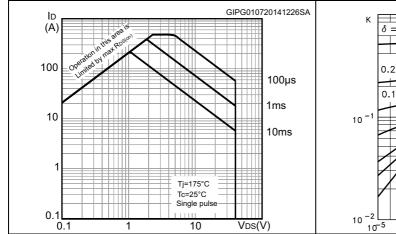
- 1. Limited by package, current allowed by silicon 177 A
- 2. Pulsed: pulse duration = $300 \mu s$, duty cycle 1.5%



Electrical characteristics (curves) 2.1

Figure 2. Safe operating area

Figure 3. Thermal impedance



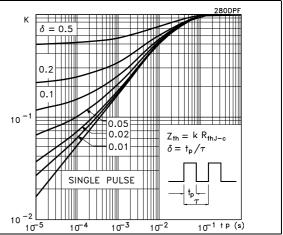
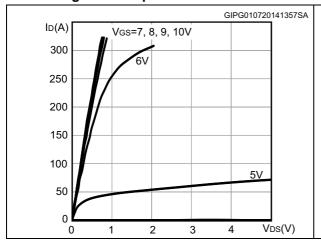


Figure 4. Output characteristics

Figure 5. Transfer characteristics



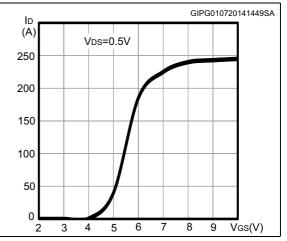
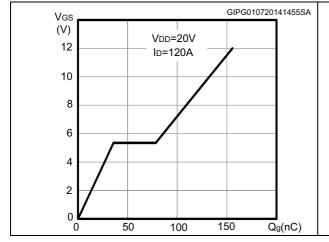
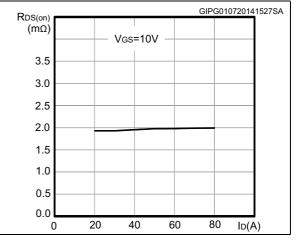


Figure 6. Gate charge vs gate-source voltage

Figure 7. Static drain-source on-resistance



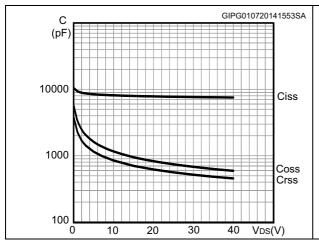


DocID027534 Rev 1

6/18

Figure 8. Capacitance variations

Figure 9. Normalized gate threshold voltage vs temperature



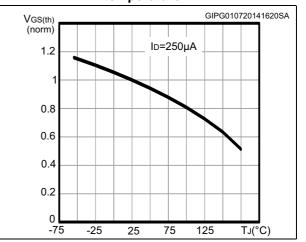
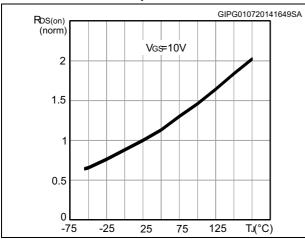


Figure 10. Normalized on-resistance vs temperature

Figure 11. Normalized $V_{(BR)DSS}$ vs temperature



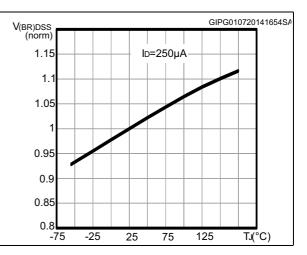
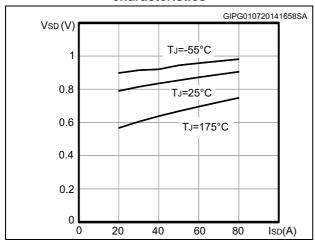


Figure 12. Source-drain diode forward characteristics





3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

57/

8/18 DocID027534 Rev 1

3.1 H²PAK-2 package information

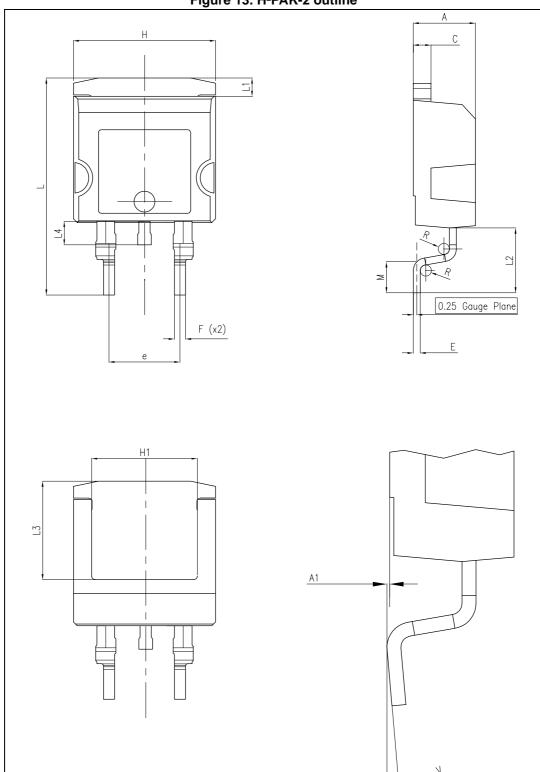


Figure 13. H²PAK-2 outline

57/

DocID027534 Rev 1

9/18

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Table 8. H²PAK-2 mechanical data

Dim.		mm	
Dim.	Min.	Тур.	Max.
А	4.30		4.80
A1	0.03]	0.20
С	1.17]	1.37
е	4.98	1	5.18
Е	0.50	1	0.90
F	0.78		0.85
Н	10.00	1	10.40
H1	7.40]	7.80
L	15.30	-	15.80
L1	1.27	1	1.40
L2	4.93		5.23
L3	6.85	1	7.25
L4	1.5	1	1.7
М	2.6	1	2.9
R	0.20	1	0.60
V	0°	<u></u>	8°

57/

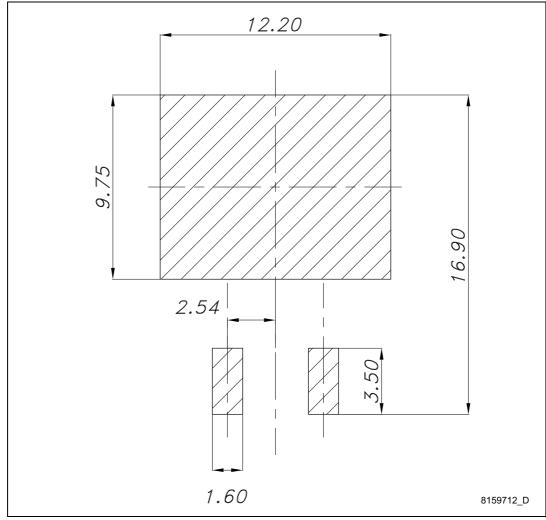


Figure 14. H²PAK-2 recommended footprint (dimensions in mm)

3.2 H²PAK-6 package information

F (x6) [3 8159693_Rev_F

Figure 15. H²PAK-6 outline

57

Table 9. H²PAK-6 mechanical data

		mm	
Dim.	Min.	Тур.	Max.
А	4.30		4.80
A1	0.03		0.20
С	1.17		1.37
е	2.34		2.74
e1	4.88		5.28
e2	7.42		7.82
Е	0.45		0.60
F	0.50		0.70
Н	10.00		10.40
H1	7.40	-	7.80
L	14.75		15.25
L1	1.27		1.40
L2	4.35		4.95
L3	6.85		7.25
L4	1.5		1.75
М	1.90		2.50
R	0.20		0.60
V	0°		8°

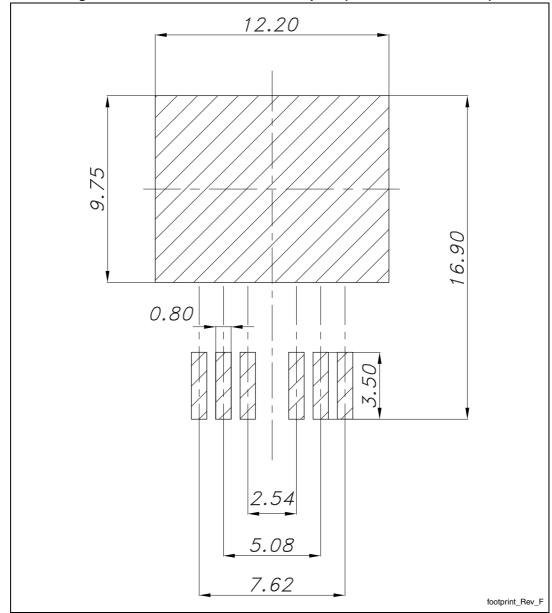


Figure 16. H²PAK-6 recommended footprint (dimensions are in mm)

577

4 Packing information

10 pitches cumulative tolerance on tape +/- 0.2 mm

Top cover properties of the prop

Figure 17. Tape dimension

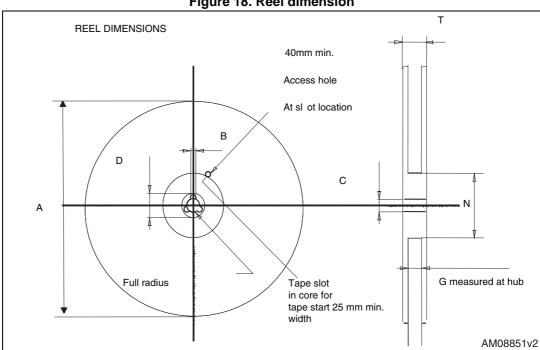


Figure 18. Reel dimension

Table 10. H²PAK-2 and H²PAK-6 tape and reel mechanical data

	Таре			Reel	
Dim.	mm		Dim.	mm	
Dim.	Min.	Max.	Diin.	Min.	Max.
A0	10.5	10.7	А		330
В0	15.7	15.9	В	1.5	
D	1.5	1.6	С	12.8	13.2
D1	1.59	1.61	D	20.2	
Е	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	Т		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
Т	0.25	0.35			
W	23.7	24.3			

16/18 DocID027534 Rev 1

5 Revision history

Table 11. Document revision history

Date	Revision	Changes
19-Feb-2015	1	First release.



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577

18/18 DocID027534 Rev 1